

SEMICONDUCTOR TECHNICAL DATA

KTD2424

EPITAXIAL PLANAR NPN TRANSISTOR

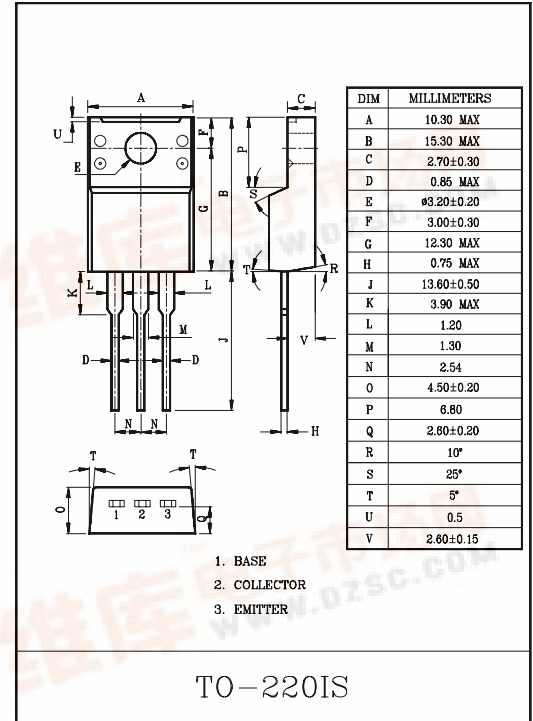
GENERAL PURPOSE DARLINGTON TRANSISTOR.

FEATURES

- High DC Current Gain : $h_{FE}=3000(\text{Min.})$ ($V_{CE}=2V$, $I_C=1A$)
- Complementary to KTB1424.

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	10	V
Collector Current	I_C	3	A
Base Current	I_B	0.5	A
Collector Power Dissipation ($T_c=25^{\circ}\text{C}$)	P_C	25	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=80V$, $I_E=0$	—	—	20	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=10V$, $I_C=0$	—	—	100	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA$, $I_B=0$	60	—	—	V
DC Current Gain	$h_{FE}(1)$	$V_{CE}=2V$, $I_C=1A$	3000	—	—	
	$h_{FE}(2)$	$V_{CE}=2V$, $I_C=3A$	1000	—	—	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	$I_C=3A$, $I_B=30mA$	—	1.5	V
	Base-Emitter	$V_{BE(sat)}$	$I_C=3A$, $I_B=30mA$	—	2.0	